



SOT-23 Plastic-Encapsulate Transistors

KTC3880S TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 150 mW ($T_{amb}=25^{\circ}C$)

Collector current

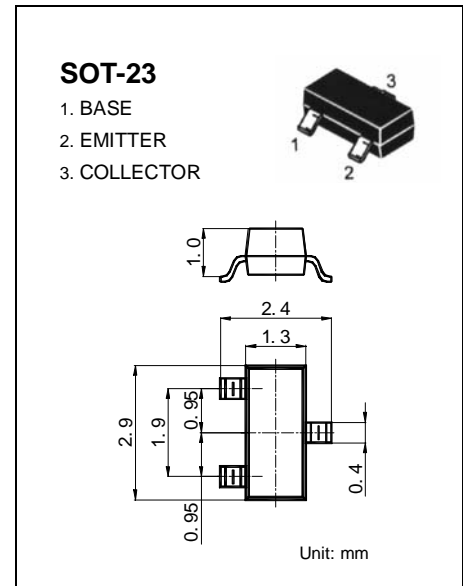
I_{CM} : 20 mA

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=18V, I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.5	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6V, I_C=1mA$	40		200	
Transition frequency	f_T	$V_{CE}=6V, I_C=1mA$		500		MHz
Collector output capacitance	C_{ob}	$V_{CB}=6V, I_E=0, f=1MHz$		1		pF
Noise figure	NF	$V_{CE}=6V, I_C=1mA, f=100MHz$			5	dB

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y
Range	40-80	70-140	100-200
Marking	AQR	AQO	AQY